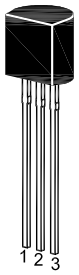
2SC1623-HAF

NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into four groups, O, Y, G and L, according to its DC current gain

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

Features

• Halogen and Antimony Free(HAF),
RoHS compliant

Absolute Maximum Ratings (T_a = 25℃)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	60	V
Collector Emitter Voltage	V_{CEO}	50	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	100	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	- 55 to + 150	℃

Dated : 08/09/2020 Rev: 01

Characteristics at T_a = 25℃

Parameter			Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at V_{CE} = 6 V, I_C = 1 mA	Current Gain Group	R O Y G	h_{FE} h_{FE} h_{FE} h_{FE}	90 135 200 300	- - - -	180 270 400 600	- - - -
Collector Base Cutoff Current at V_{CB} = 60 V			I_{CBO}	-	-	0.1	μA
Emitter Base Cutoff Current at V_{EB} = 5 V			I_{EBO}	-	-	0.1	μA
Collector Base Breakdown Voltage at I_C = 100 μA			$V_{(BR)CBO}$	60	-	-	V
Collector Emitter Breakdown Voltage at I_C = 10 mA			$V_{(BR)CEO}$	50	-	-	V
Emitter Base Breakdown Voltage at I_E = 10 μA			$V_{(BR)EBO}$	5	-	-	V
Collector Emitter Saturation Voltage at I_C = 100 mA, I_B = 10 mA			$V_{CE(sat)}$	-	0.15	0.3	V
Base Emitter Saturation Voltage at I_C = 100 mA, I_B = 10 mA			$V_{BE(sat)}$	-	0.86	1	V
Gain Bandwidth Product at V_{CE} = 6 V, I_C = 10 mA			f_T	-	250	-	MHz
Output Capacitance at V_{CB} = 6 V, f = 1 MHz			C_{ob}	-	3	-	pF